



650V/ 15A Silicon Carbide Power Schottky Barrier Diode

Features

- Zero reverse recovery current
- Zero forward recovery voltage
- Temperature independent switching behavior
- High temperature operation
- High frequency operation

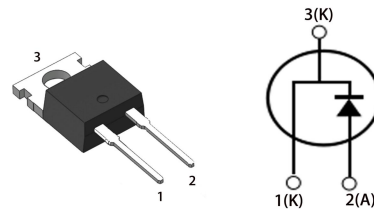
Benefits

- Unipolar rectifier
- Substantially reduced switching losses
- No thermal run-away with parallel devices
- Reduced heat sink requirements

Applications

- SMPS, e.g., CCM PFC;
- Motor drives, Solar application, UPS, Wind turbine, Rail traction, EV/HEV

| Key Characteristics | | |
|-----------------------------------|------------|-----------|
| V_{RRM} | 650 | V |
| $I_F, T_c \leq 143^\circ\text{C}$ | 15 | A |
| Q_c | 31 | nC |



| Part No. | Package Type | Marking |
|------------|--------------|------------|
| G4S06515AT | TO-220AC | G4S06515AT |

Maximum Ratings

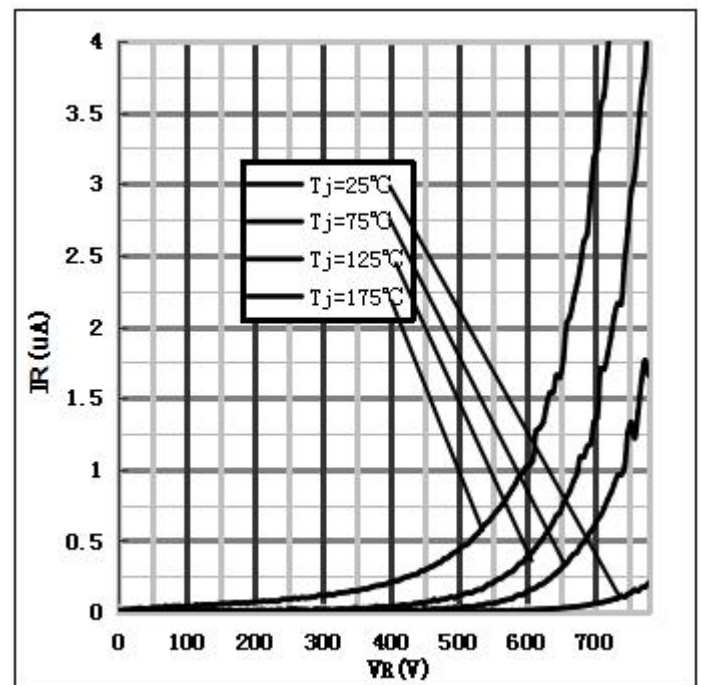
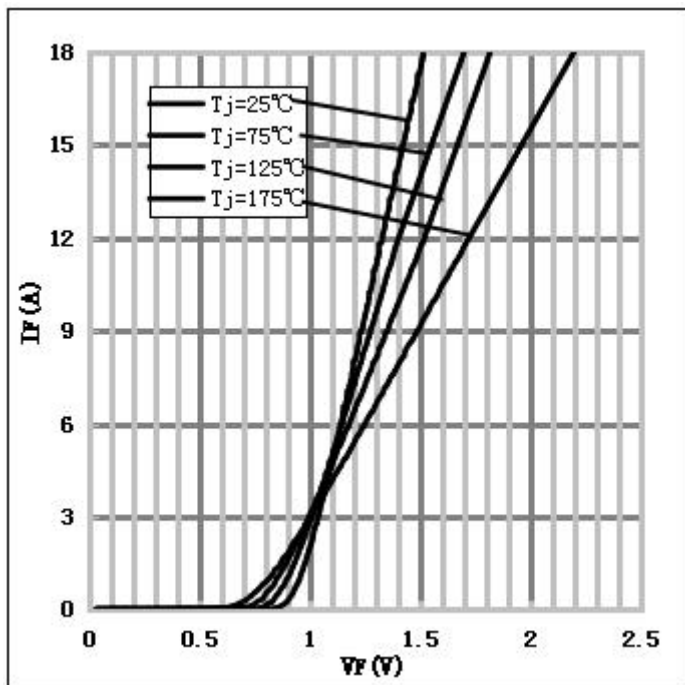
| Parameter | Symbol | Test Condition | Value | Unit |
|---|-----------|---|----------------|--------|
| Repetitive Peak Reverse Voltage | V_{RRM} | | 650 | V |
| Surge Peak Reverse Voltage | V_{RSM} | | 650 | V |
| DC Blocking Voltage | V_{DC} | | 650 | V |
| Continuous Forward Current | I_F | $T_C=25^{\circ}C$ $T_C=125^{\circ}C$ $T_C=143^{\circ}C$ | 36 19 15 | A |
| Repetitive Peak Forward Surge Current | I_{FRM} | $T_C=25^{\circ}C$, $t_p=10ms$, Half Sine Wave, $D=0.3$ | 50 | A |
| Non-repetitive Peak Forward Surge Current | I_{FSM} | $T_C=25^{\circ}C$, $t_p=10ms$, Half Sine Wave | 130 | A |
| Power Dissipation | P_{TOT} | $T_C=25^{\circ}C$ | 129 | W |
| | | $T_C=110^{\circ}C$ | 56 | W |
| Operating Junction | T_j | | -55°C to 175°C | °C |
| Storage Temperature | T_{stg} | | -55°C to 175°C | °C |
| Mounting Torque | | M3 Screw | 1 | Nm |
| | | 6-32 Screw | 8.8 | lbf-in |

Thermal Characteristics

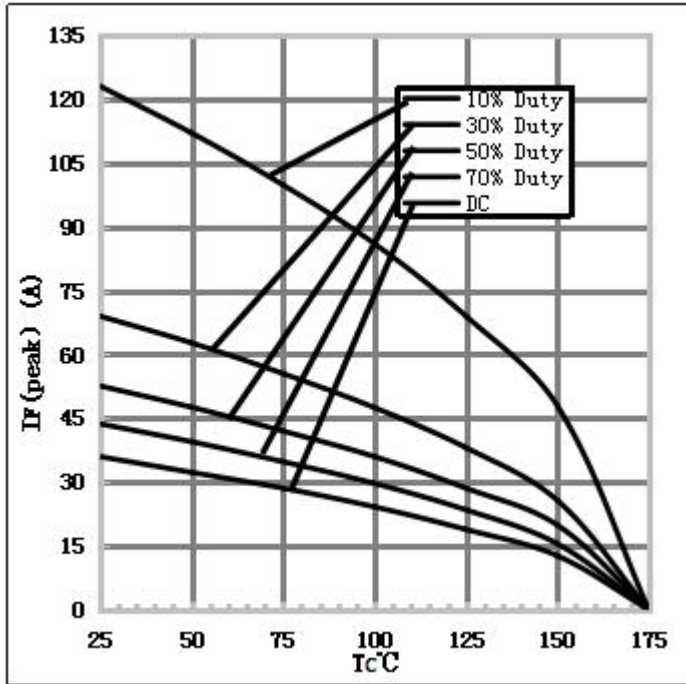
| Parameter | Symbol | Test Condition | Value | Unit |
|--|------------|----------------|-------|------|
| | | | Typ. | |
| Thermal resistance from junction to case | R_{thJC} | | 1.16 | °C/W |

Electrical Characteristics

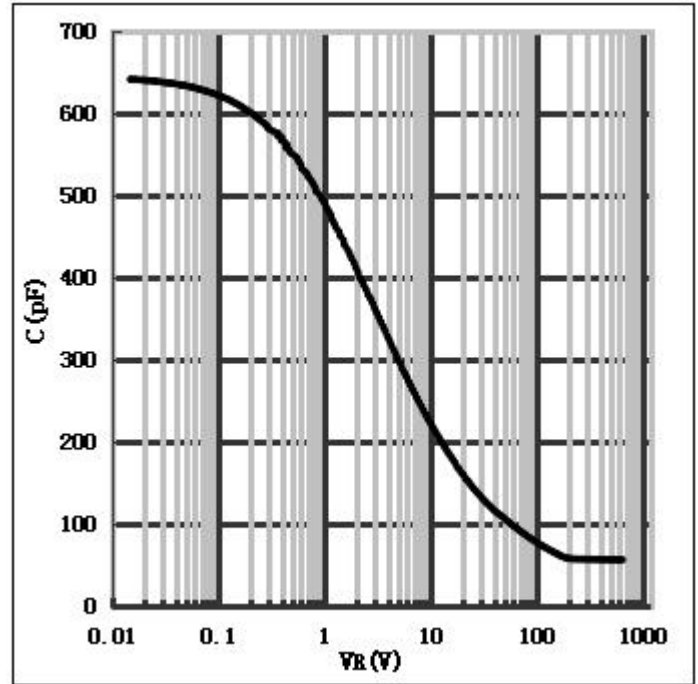
| Parameter | Symbol | Test Conditions | Numerical | | Unit |
|-------------------------|--------|--|-----------|------|---------|
| | | | Typ. | Max. | |
| Forward Voltage | V_F | $I_F=15A, T_j=25^\circ C$ | 1.5 | 1.7 | V |
| | | $I_F=15A, T_j=175^\circ C$ | 2 | 2.5 | |
| Reverse Current | I_R | $V_R=650V, T_j=25^\circ C$ | 0.5 | 50 | μA |
| | | $V_R=650V, T_j=175^\circ C$ | 1.4 | 100 | |
| Total Capacitive Charge | Q_C | $V_R=400V, T_j=150^\circ C$ $Q_C = \int_0^{V_R} C(V)dV$ | 31 | - | nC |
| Total Capacitance | C | $V_R=0V, T_j=25^\circ C, f=1MHz$ | 645 | 680 | pF |
| | | $V_R=200V, T_j=25^\circ C, f=1MHz$ | 58 | 61 | |
| | | $V_R=400V, T_j=25^\circ C, f=1MHz$ | 56 | 58 | |

Performance Graphs1) Forward IV characteristics as a function of T_j :2) Reverse IV characteristics as a function of T_j :

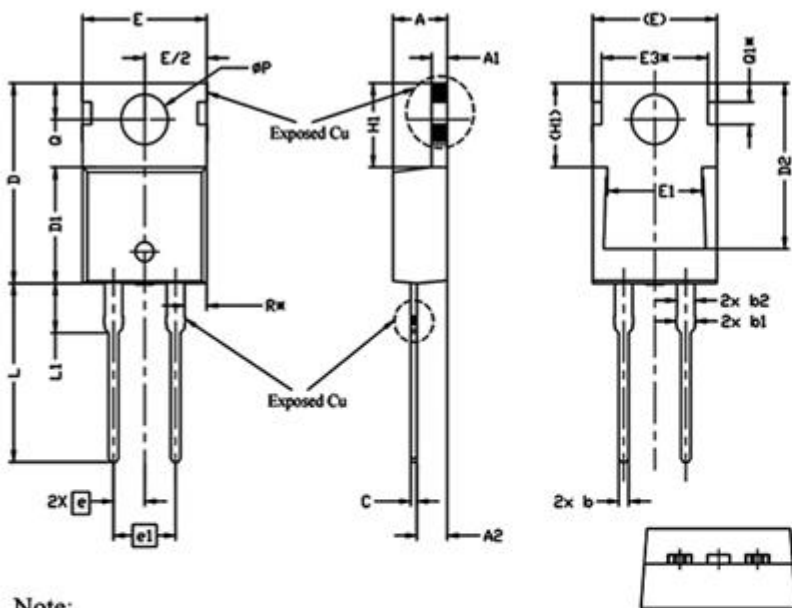
3) Current Derating:



4) Capacitance vs. reverse voltage:



Package TO-220AC



Note:

1. Package Reference: JEDEC TO220, Variation AB.
2. All Dimensions Are In mm.
3. Slot Required, Notch May Be Rounded
4. Dimension D & E Do Not Include Mold Flash. Mold Flash Shall Not Exceed 0.127mm Pre Side. These Dimensions Are Measured At The Outermost Extreme Of The Plastic Body.
5. Thermal Pad Contour Optional Within Dimensions E, H1, D2 & E1.
6. Dimension E2 & H1 Define A Zone Where Stamping And Singulation Irregularities Are Allowed.
7. "*" is reference .

单位: mm

| SYMBOL | DIMENSIONS | | | NOTES |
|--------|------------|-------|-------|-------|
| | MIN. | NOM. | MAX. | |
| A | 4.24 | 4.44 | 4.64 | |
| A1 | 1.15 | 1.27 | 1.40 | |
| A2 | 2.30 | 2.48 | 2.70 | |
| b | 0.70 | 0.80 | 0.90 | |
| b1 | 1.20 | 1.55 | 1.75 | |
| b2 | 1.20 | 1.45 | 1.70 | |
| c | 0.40 | 0.50 | 0.60 | |
| D | 14.70 | 15.37 | 16.00 | 4 |
| D1 | 8.82 | 8.92 | 9.02 | |
| D2 | 12.63 | 12.73 | 12.83 | 5 |
| E | 9.96 | 10.16 | 10.36 | 4,5 |
| E1 | 6.86 | 7.77 | 8.89 | 5 |
| E3* | 8.70REF. | | | |
| e | 2.54BSC | | | |
| e1 | 5.08BSC | | | |
| H1 | 6.30 | 6.45 | 6.60 | 5,6 |
| L | 13.47 | 13.72 | 13.97 | |
| L1 | 3.60 | 3.80 | 4.00 | |
| ∅P | 3.75 | 3.84 | 3.93 | |
| Q | 2.60 | 2.80 | 3.00 | |
| Q1* | 1.73REF. | | | |
| R* | 1.82REF. | | | |

Note: The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC(RoHS2). RoHS Certification and other certifications can be obtained from GPT sales representatives or GPT website: <http://globalpowertech.cn/English/index.asp>

More product datasheets and company information can be found in:

<http://globalpowertech.cn/English/index.asp>

